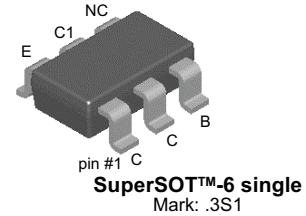


# FMBS5551

## NPN General Purpose Amplifier

- This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.



## Absolute Maximum Ratings\* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current - Continuous	600	mA
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	- 55 ~ 150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
<b>Off Characteristics</b>					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage *	$I_C = 1.0\text{mA}, I_B = 0$	160		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	180		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_a = 100^\circ\text{C}$		50 50	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 4.0\text{V}, I_C = 0$		50	nA
<b>On Characteristics</b>					
$h_{FE}$	DC Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$	80 80 30	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		0.15 0.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		1.0 1.0	V
<b>Small Signal Characteristics</b>					
$f_T$	Current Gain Bandwidth Product	$I_C = 10\text{mA}, V_{CE} = 10, f = 100\text{MHz}$	100	300	MHz
$C_{obo}$	Output Capacitance	$V_{CE} = 10\text{V}, I_C = 0, f = 1.0\text{MHz}$		6.0	pF
$C_{ibo}$	Input Capacitance	$V_{BE} = 0.5\text{V}, I_C = 0, f = 1.0\text{MHz}$		20	pF
$h_{fe}$	Small Single Current Gain	$I_C = 1.0\text{mA}, V_{CE} = 10\text{V}, f = 1.0\text{KHz}$	50	250	
$N_F$	Noise Figure	$I_C = 250\mu\text{A}, V_{CE} = 5.0\text{V},$ $R_S = 1.0\text{K}\Omega, f = 10\text{ Hz to } 15.7\text{KHz}$		8.0	dB

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**Thermal Characteristics**  $T_a=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Max.	Units
$P_D$	Total Device Dissipation *	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	$^\circ\text{C}/\text{W}$

\* Device mounted on a 1 in 2 pad of 2 oz copper.

# Typical Characteristics

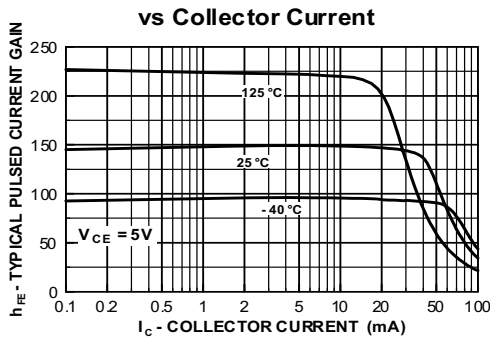


Figure 1. Typical Pulsed Current Gain vs Collector Current

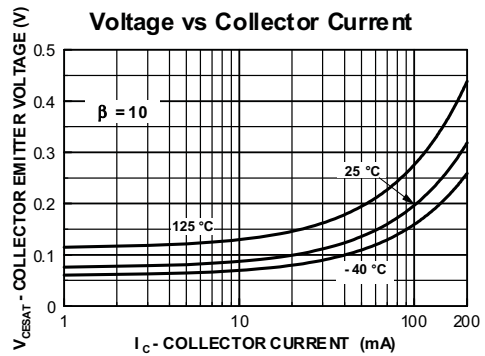


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

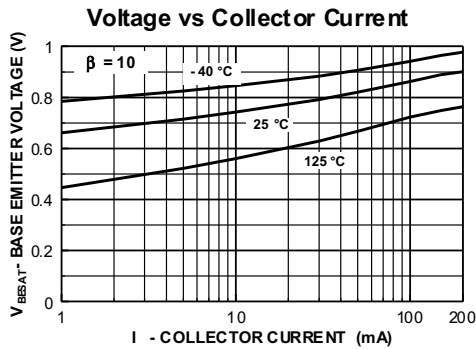


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

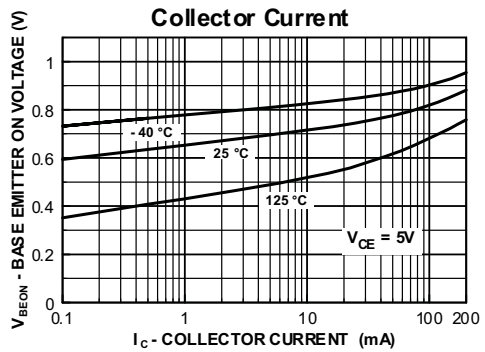


Figure 4. Base-Emitter On Voltage vs Collector Current

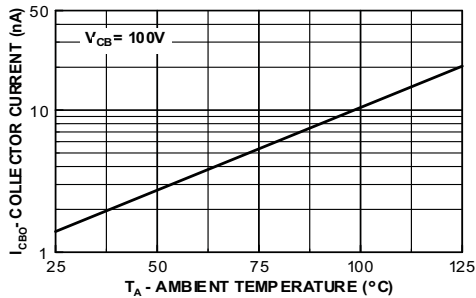


Figure 5. Collector Cutoff Current vs Ambient Temperature

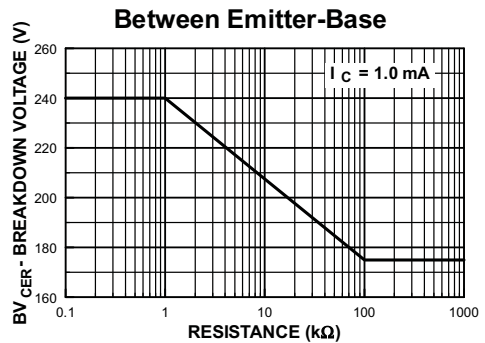


Figure 6. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

Typical Characteristics (Continued)

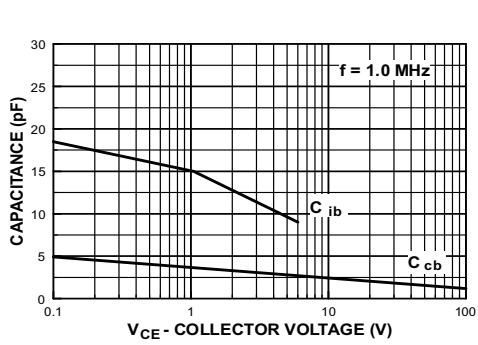


Figure 7. Input and Output Capacitance vs Reverse Voltage

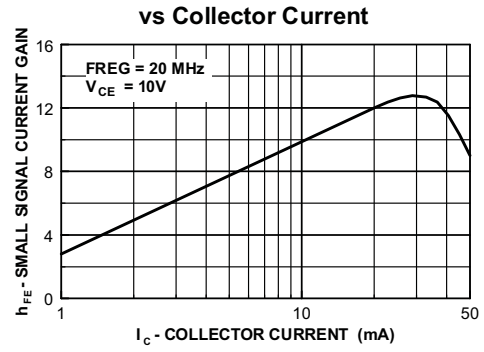
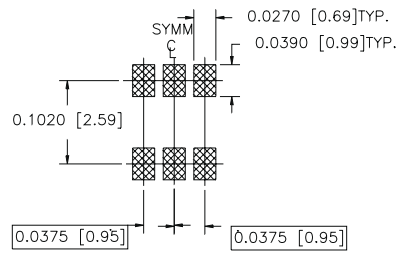
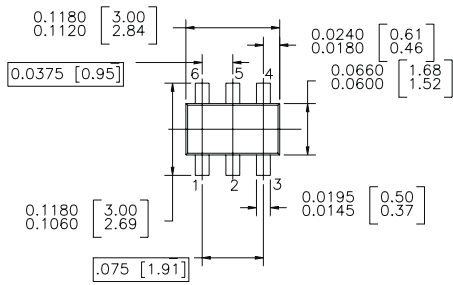


Figure 8. Small Signal current Gain vs Collector Current

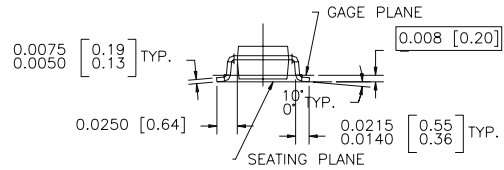
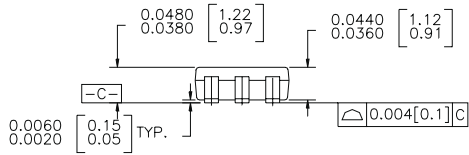
# Package Dimensions

## SuperSOT™-6



LAND PATTERN RECOMMENDATION

CONTROLLING DIMENSION IS INCH  
VALUES IN [ ] ARE MILLIMETERS



SUPER SOT 6 LEADS

- NOTES : UNLESS OTHERWISE SPECIFIED
- 1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS)  
MINIMUM TIN / LEAD (SOLDER) ON COPPER.
  - 2.0 NO JEDEC REGISTRATION AS OF JULY 1996

Dimensions in Millimeters

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Bottomless™	FPS™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CoolFET™	FRFET™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET®	SuperSOT™-8
DOME™	GTO™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic®
E <sup>2</sup> CMOS™	I <sup>2</sup> C™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC®	μSerDes™	UltraFET®
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	VCX™
The Power Franchise®		PACMAN™	SMART START™	
Programmable Active Droop™		POP™	SPM™	

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## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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